

Please amend the subject application as follows:

IN THE SPECIFICATION:

On pages 6 and 7, amend the paragraph beginning at line 18 and extending to page 7, line 12 as follows:

Illustrated in FIG. 6 is a cross-section of further processing of semiconductor device 10 that is a continuation of the processing of FIG. 4. In FIG. 6, a directional implant 38 of a second conductivity type (P or N, depending upon the first implant), i.e. a second species, is performed from a second and different direction within the implant chamber. The direction of the implant is again important as it should be noted that the directional implant 38 forms a third implant region 40 in a second area adjacent the fin structure 24 that is different than the first area and forms a fourth implant region 42. The important resulting feature of directional implant 38 is that no implant region is formed on the immediate left hand side of the fin structure 24 as a result of this implant step. The third implant region 40 adjoins fin structure 24 on only one side and over the top region of fin structure 24 within polysilicon layer 28. This directional feature is important as an implant is performed in a manner that does not uniformly surround the fin structure 24 with the same doping species. Therefore, at this point two physically separate or non-contiguous implants of differing conductivities are present around the fin structure 24. It should be understood that although separate conductivities are preferred, the same conductivity type with differing doses may be used in some applications depending upon the structure being formed. The depth of the implants illustrated herein are is not necessarily drawn to scale and will vary depending upon the specifications of the device being fabricated.